BLC9G27LS-151AV

Power LDMOS transistor

AMPLEON

Rev. 2 — 2 December 2016

Product data sheet

1. Product profile

1.1 General description

150 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in the Doherty demo board.

Test signal	f	V _{DS}	P _{L(AV)}	Gp	η_{D}	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2496 to 2690	28	28.2	15.5	48	-30 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 RF power amplifier for LTE base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)			1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4 4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLC9G27LS-151AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-3			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-case)}	thermal resistance from junction to case	T_{case} = 80 °C; I_{Dq} = 280 mA; $V_{GS(amp)\ peak}$ = 0.85 V		
		P _L = 28.2 W	0.314	K/W
		P _L = 44.7 W	0.270	K/W

6. Characteristics

 Table 6.
 DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice		-			
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.5 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 50 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 300mA	1.75	2.3	2.85	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	10.9	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 50 mA	-	0.53	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.75 \text{ A}$	-	285	460	mΩ
Peak dev	vice	1				
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.1 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 110 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 660 mA	1.65	2.2	2.75	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	23.8	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 110 mA	-	1.16	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.85 \text{ A}$	-	130	215	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2496 MHz; f_2 = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 280 mA (main); $V_{GS(amp)peak}$ = 0.8 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 28 W	14.4	15.6	-	dB
RLin	input return loss	P _{L(AV)} = 28 W	-	-11	-7	dB
η_{D}	drain efficiency	P _{L(AV)} = 28 W	41	46	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 28 W	-	-30	-25	dBc

Table 8. RF characteristics

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; f = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 280 mA (main); $V_{GS(amp)peak}$ = 0.8 V; T_{case} = 25 °C; unless otherwise specified; tested in an asymmetrical Doherty production test circuit at frequencies from 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression		135	155	-	W

Test information

Ruggedness in Doherty operation

The BLC9G27LS-151AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.85 V; P_L = 50 W (1-carrier W-CDMA); f = 2496 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]				
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)				
Maximum pov	Maximum power load								
2496	6.2 – j7.7	3.3 – j7.7	71.5	55.8	18.1				
2600	6.1 – j5.9	3.3 – j7.7	71.3	55.7	18.5				
2690	3.6 – j5.4	3.3 – j7.7	66.9	54.9	19.1				
Maximum dra	in efficiency load								
2496	6.2 – j7.7	6.4 – j5.7	52.8	63.5	20.3				
2600	6.1 – j5.9	6.0 – j5.9	52.1	64.3	21.1				
2690	3.6 – j5.4	5.0 – j5.0	48.5	61.8	21.5				

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 600 mA (peak); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]				
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)				
Maximum pov	Maximum power load								
2496	7.2 – j8.6	4.1 – j9.1	146.9	58.2	17.6				
2600	8.0 – j6.3	4.1 – j9.1	141.1	56.0	17.9				
2690	6.0 – j2.8	5.0 – j10.0	137.3	55.7	18.3				
Maximum dra	in efficiency load								
2496	7.2 – j8.6	5.8 – j6.2	115.5	65.3	19.5				
2600	8.0 – j6.3	5.4 – j5.5	103.2	64.2	20.2				
2690	6.0 – j2.8	4.8 – j5.9	98.5	62.8	20.6				

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.

42.0

19.3

Power LDMOS transistor

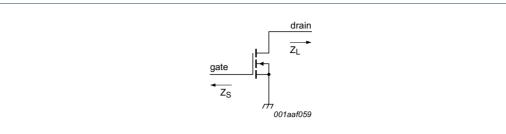


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device; $I_{Dq} = 300 \text{ mA (main)}$; $V_{DS} = 28 \text{ V}$.

 $Z_{\rm S}$ [1] Z_{l} [1] P₁ [2] G_p [3] η_D [3] (MHz) (Ω) (dBm) (%) (dB) (Ω) 2496 6.2 - j7.73.7 - j7.048.1 41.5 18.5 2600 6.1 - j5.93.7 - j7.148.0 42.0 18.7

48.0

[1] Z_S and Z_L defined in Figure 1.

3.6 - j5.4

- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

2690

Table 12. Typical impedance of main device at 1: 2.5 load

Measured load-pull data of main device; I_{Dq} = 300 mA (main); V_{DS} = 28 V.

3.7 - j7.2

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	6.2 – j7.7	6.8 – j12.9	46.2	55	20.7
2600	6.1 – j5.9	6.0 – j14.1	46.7	54	21.3
2690	3.6 – j5.4	5.5 – j13.7	45.9	53	21.8

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

7.4 VBW in Doherty operation

The BLC9G27LS-151AV shows 100 MHz (typical) video bandwidth in Doherty demo board in 2600 MHz at V_{DS} = 28 V; I_{Dq} = 250 mA and $V_{GS(amp)peak}$ = 0.8 V.

7.5 Test circuit

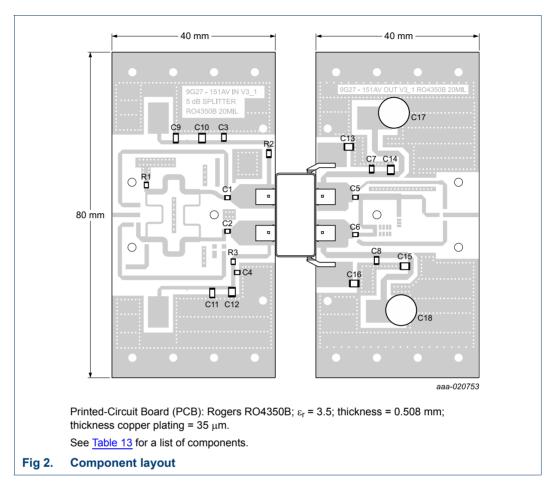


Table 13. List of components See Figure 2 for component layout.

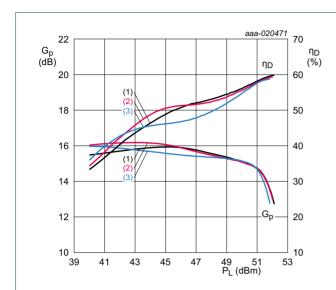
Component	Description	Value	Remarks
C1, C2, C3, C4, C6, C7, C8	multilayer ceramic chip capacitor	9.1 pF [1]	
C5	multilayer ceramic chip capacitor	4.3 pF [1]	
C9, C11	multilayer ceramic chip capacitor	1 μF, 50 V [2]	
C10, C12, C13, C14, C15, C16	multilayer ceramic chip capacitor	10 μF, 50 V [2]	
C17, C18	electrolytic capacitor	1000 μF, 100 V	
R1	resistor	51 Ω	SMD 0805
R2. R3	resistor	9.1 Ω	SMD 0805

^[1] American Technical Ceramics type 600F or capacitor of same quality

^[2] Murata or capacitor of same quality

7.6 Graphical data

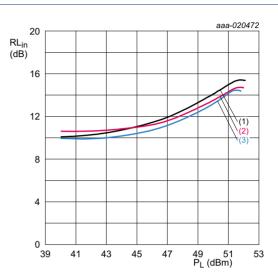
7.6.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 210 mA (main device); $V_{GS(amp)peak}$ = 0.85 V.

- (1) f = 2496 MHz
- (2) f = 2590 MHz
- (3) f = 2690 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

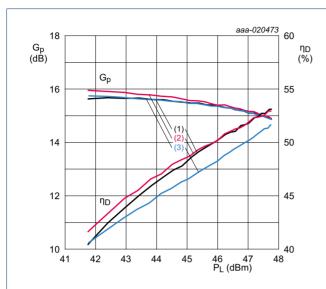


 V_{DS} = 28 V; I_{Dq} = 210 mA (main device); $V_{GS(amp)peak}$ = 0.85 V.

- (1) f = 2496 MHz
- (2) f = 2590 MHz
- (3) f = 2690 MHz

Fig 4. Input return loss as a function of output power; typical values

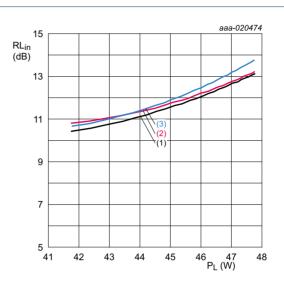
7.6.2 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 210 mA (main device); $V_{GS(amp)peak}$ = 0.85 V.

- (1) f = 2496 MHz
- (2) f = 2590 MHz
- (3) f = 2690 MHz

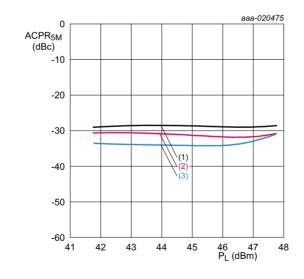
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 210 mA (main device); $V_{GS(amp)peak}$ = 0.85 V.

- (1) f = 2496 MHz
- (2) f = 2590 MHz
- (3) f = 2690 MHz

Fig 6. Input return loss as a function of output power; typical values

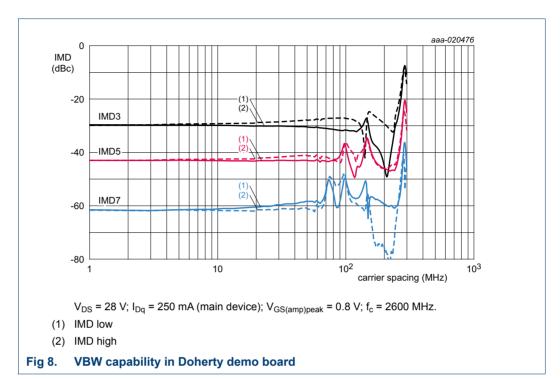


 V_{DS} = 28 V; I_{Dq} = 210 mA (main device); $V_{GS(amp)peak}$ = 0.85 V.

- (1) f = 2496 MHz
- (2) f = 2590 MHz
- (3) f = 2690 MHz

Fig 7. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

7.6.3 2-Tone VBW



8. Package outline

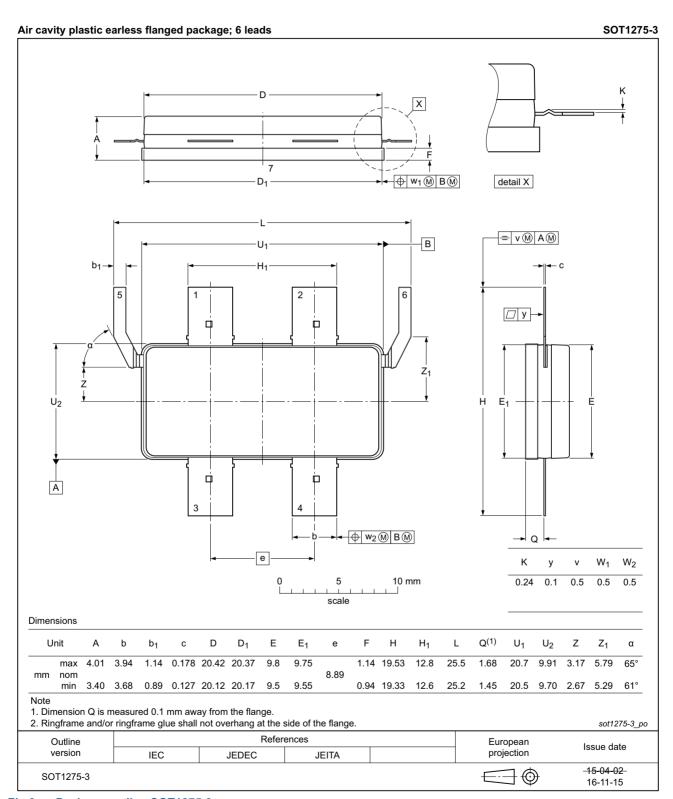


Fig 9. Package outline SOT1275-3

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

^[1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G27LS-151AV v.2	20161202	Product data sheet	-	BLC9G27LS-151AV v.1
Modifications:	 Figure 9 on page 10: updated package outline drawing SOT1275-3 Section 9 on page 11: updated Handling information 			
BLC9G27LS-151AV v.1	20160226	Product data sheet	-	-

^[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

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12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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